# ne<mark>x</mark>peria

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

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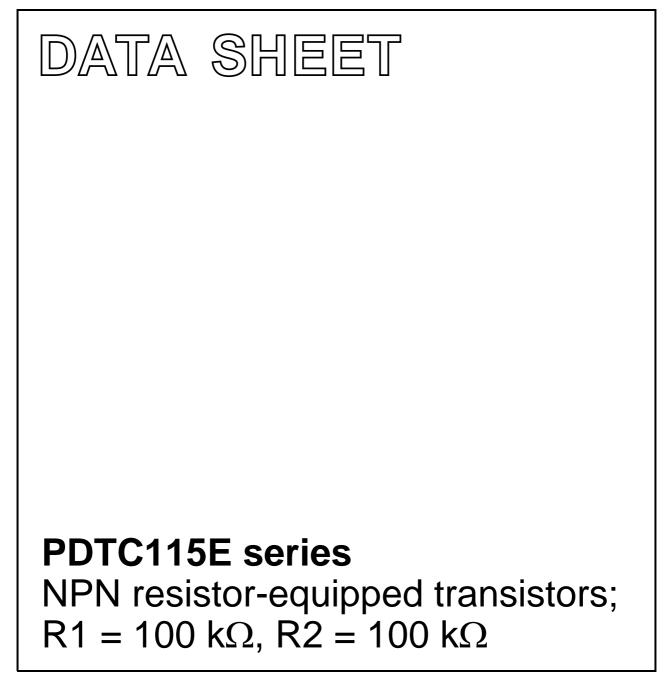
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 Apr 06 2004 Aug 06



## **PDTC115E series**

#### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

**PRODUCT OVERVIEW** 

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT	
V <sub>CEO</sub>	collector-emitter voltage	-	50	V	
lo	output current (DC)	-	20	mA	
R1	bias resistor	100	-	kΩ	
R2	bias resistor	100	-	kΩ	

### DESCRIPTION

NPN resistor equipped transistor (see "Simplified outline, symbol and pinning" for package details).

TYPE NUMBER	PACKAGE				
	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT	
PDTC115EE	SOT416	SC-75	46	PDTA115EE	
PDTC115EEF	SOT490	SC-89	49	PDTA115EEF	
PDTC115EK	SOT346	SC-59	56	PDTA115EK	
PDTC115EM	SOT883	SC-101	DV	PDTA115EM	
PDTC115ES	SOT54 (TO-92)	SC-43	TC115E	PDTA115ES	
PDTC115ET	SOT23	_	*44 <sup>(1)</sup>	PDTA115ET	
PDTC115EU	SOT323	SC-70	*15 <sup>(1)</sup>	PDTA115EU	

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

## PDTC115E series

## SIMPLIFIED OUTLINE, SYMBOL AND PINNING

			PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION		
PDTC115ES		1 2 3	base collector emitter		
PDTC115EE		1	base		
PDTC115EEF		2	emitter		
PDTC115EK PDTC115ET PDTC115EU		3	collector		
	1   2     Top view   MDB269				
PDTC115EM		1	base		
		2	emitter		
	2 1 bottom view MHC506	3	collector		

## PDTC115E series

#### **ORDERING INFORMATION**

		PACKAGE			
TYPE NUMBER	NAME	DESCRIPTION			
PDTC115EE	-	plastic surface mounted package; 3 leads	SOT416		
PDTC115EEF	-	<ul> <li>plastic surface mounted package; 3 leads</li> </ul>			
PDTC115EK	-	<ul> <li>plastic surface mounted package; 3 leads</li> </ul>			
PDTC115EM	- leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm		SOT883		
PDTC115ES	<ul> <li>plastic single-ended leaded (through hole) package; 3 leads</li> </ul>		SOT54		
PDTC115ET	<ul> <li>plastic surface mounted package; 3 leads</li> </ul>		SOT23		
PDTC115EU	-	plastic surface mounted package; 3 leads			

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
lo	output current (DC)		-	20	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT883	notes 2 and 3	_	250	mW
	SOT490	notes 1 and 2	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

## PDTC115E series

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT833	notes 2 and 3	500	K/W
	SOT490	notes 1 and 2	500	K/W

#### Notes

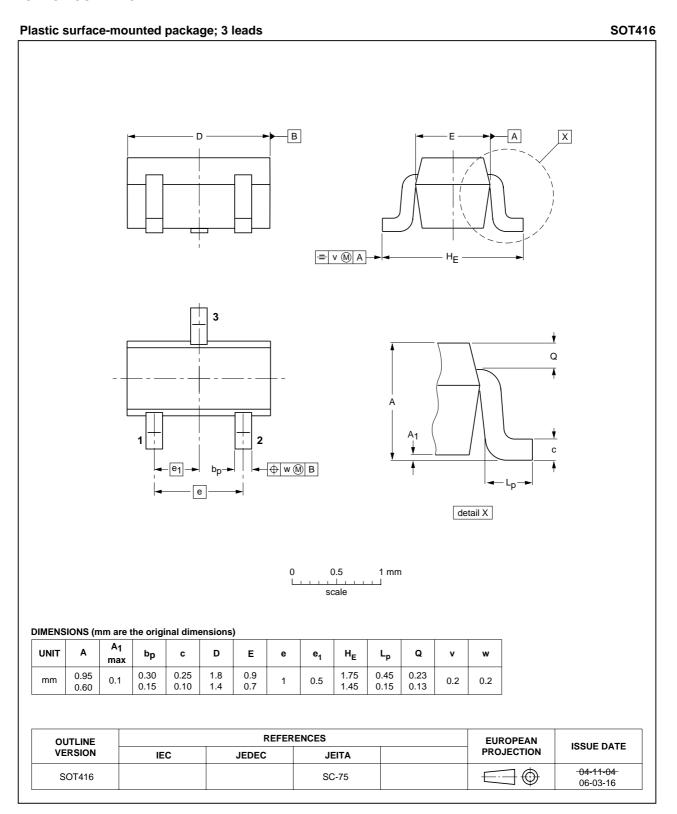
- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

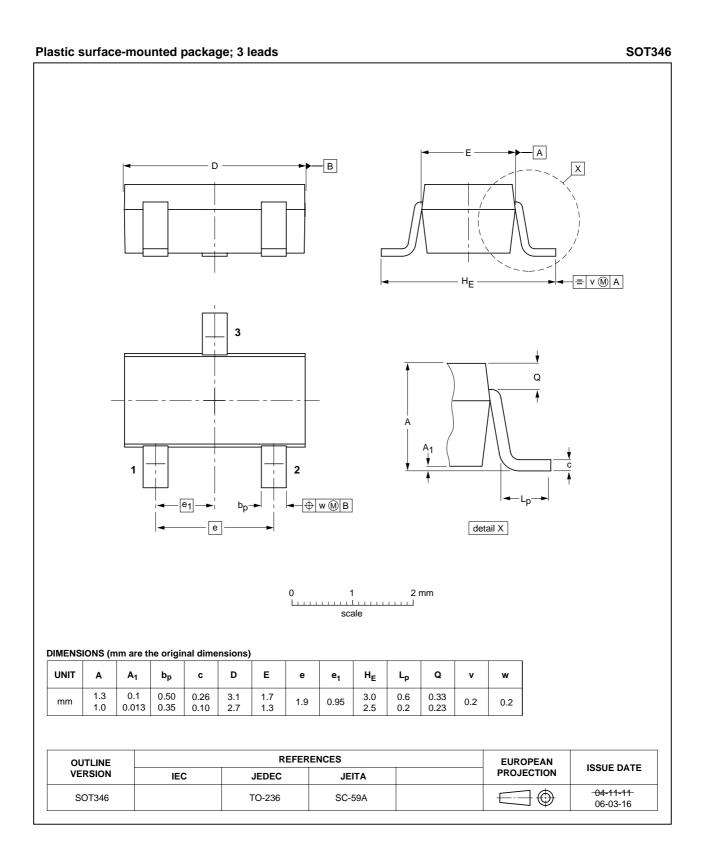
#### CHARACTERISTICS

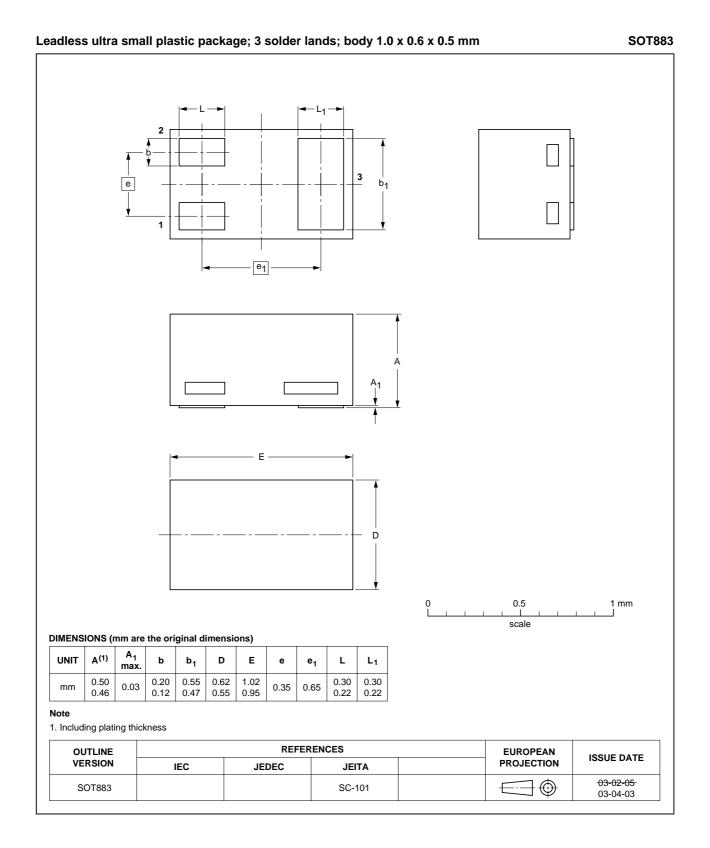
 $T_{amb}$  = 25 °C unless otherwise specified.

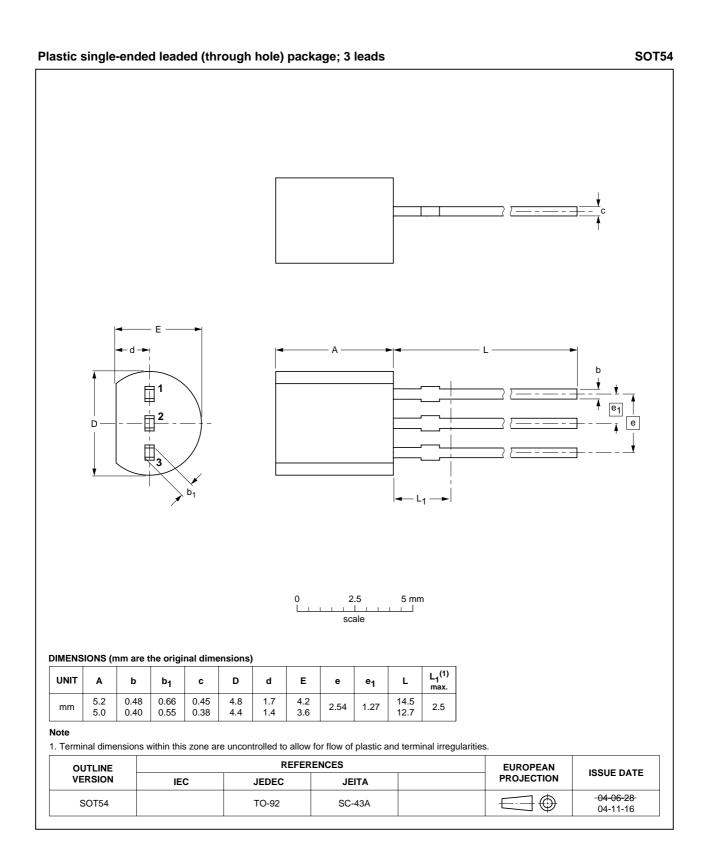
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	_	_	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A	_	_	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	_	_	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A	-	-	50	μA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 5 mA; I <sub>B</sub> = 0.25 mA	_	_	150	mV
V <sub>i(off)</sub>	input-off voltage	$I_{C} = 100 \ \mu A; V_{CE} = 5 \ V$	-	1.1	0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 0.3 V	3	1.5	-	V
R1	input resistor		70	100	130	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	_	2.5	pF

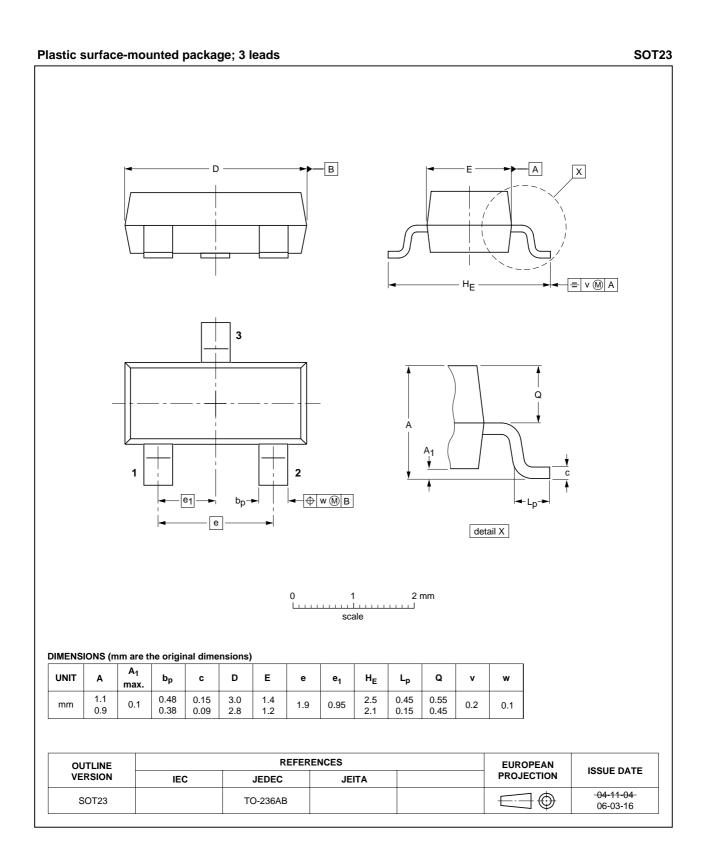
## PACKAGE OUTLINES

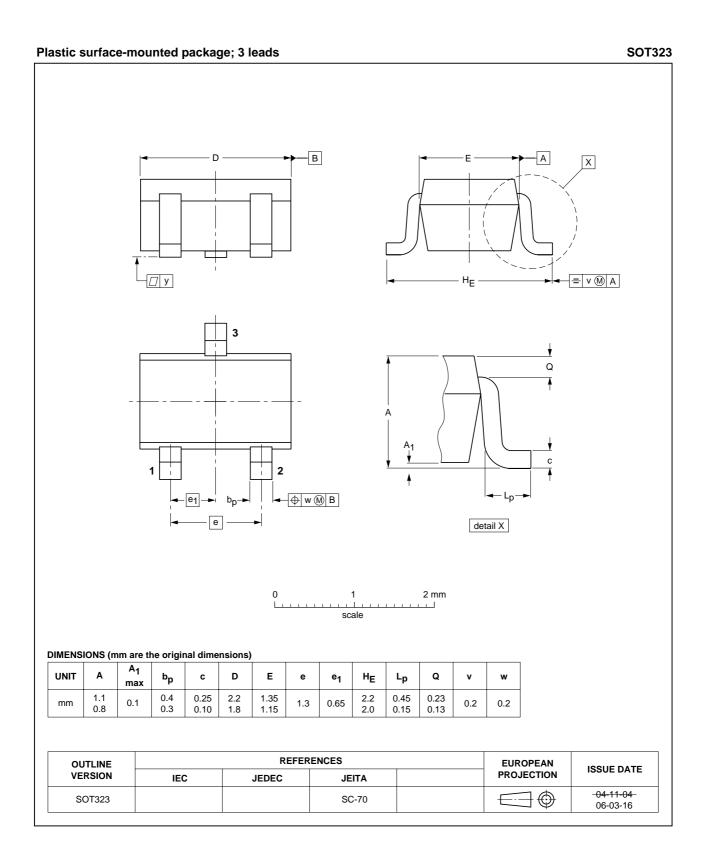


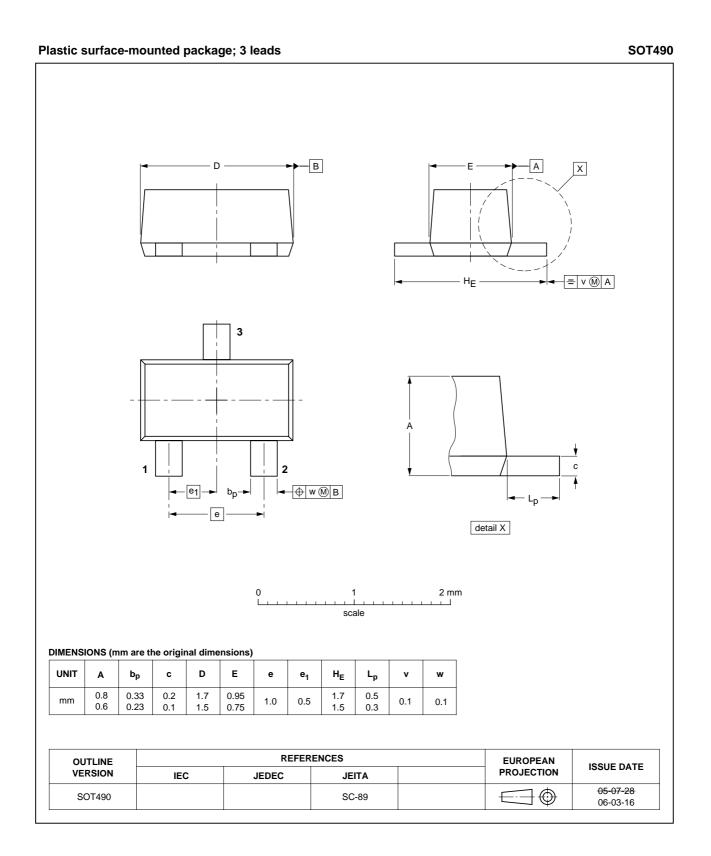












## PDTC115E series

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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# **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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